

IN THE CLAIMS:

1. (Currently Amended) A hybrid substrate comprising:
a substrate having a plurality of pockets patterned thereon; and
at least two different ~~materials-provided~~ material arrangements deposited within a
respective pocket of the plurality of pockets.
2. (Currently Amended) The hybrid substrate according to Claim 1, wherein
the at least two different ~~materials~~ material arrangements are approximately co-planar
with a top surface of the substrate.
3. (Currently Amended) The hybrid substrate according to Claim 1, wherein
the at least two different ~~materials~~ material arrangements are bonded to the substrate.
4. (Currently Amended) The hybrid substrate according to Claim 1, wherein
each of the at least two different ~~materials~~ material arrangements is selected from the
group consisting of GaAs, InP, silicon wafer, GaN-based high-electron mobility
transistors (HEMTs), and optoelectronic devices.
5. (Original) The hybrid substrate according to Claim 1, wherein the
substrate is selected from the group consisting of AlN, quartz, glass, ceramic, CVD
diamond, and sapphire.
6. (Original) The hybrid substrate according to Claim 1, wherein the

substrate is a high thermal conductive substrate.

7. (Currently Amended) The hybrid substrate according to Claim 1, wherein each of the plurality of pockets has a greater surface area than ~~a cross-section~~ surface area of a cross-section of the at least two different ~~materials~~ material arrangements, the cross-section being parallel to a surface of the hybrid substrate.

8-18. (Currently Withdrawn)